

[AN ANTI-FUSE STRUCTURE WITH LOW ON-STATE RESISTANCE AND LOW OFF- STATE LEAKAGE]

Abstract of Disclosure

An anti-fuse structure is set on an isolation layer positioned on a substrate. The anti-fuse structure includes a silicon conductive layer positioned in the isolation layer, a dielectric layer positioned on the top surface of the silicon conductive layer, and a metal conductive layer positioned on the surface of the isolation layer and covering the dielectric layer.

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Figures

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